

ABSTRACT OF THE DISCLOSURE

A method for sensing a signal received from an array cell within a memory array, the method comprising the steps of generating an analog voltage V_{ddr} proportional to a current of a selected array cell of the memory array, and comparing the analog voltage V_{ddr} with a reference analog voltage V_{comp} to generate an output digital signal. A method is also provided for sensing a memory cell by transforming a signal from a memory cell to a time delay, and sensing the memory cell by comparing the time delay to a time delay of a reference cell. Related apparatus is also disclosed.